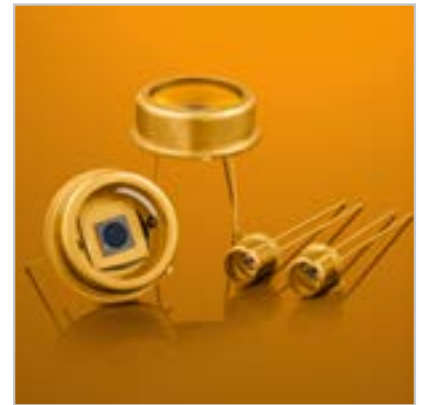


Silicon Avalanche Photodiode SAT-Series

Description

The SAT-Series is based on a “reach-through” structure for excellent quantum efficiency, high speed and targeted for the 1060 nm detection region. The chip is hermetically sealed in a modified TO-8 / TO-5 package.

This APD is also available in a hermetically sealed TO-37 with thermo-electrical cooler. This enables the APD to be used in a variety of demanding applications including LIDAR and medical applications.



Features

- Very high 1060 nm quantum efficiency
- Low noise, high speed
- Multiplication gain, $M > 100$ available
- 800 μm or 3.0 mm diameter active area
- Gradual multiplication curve
- Wide operating temperature range

Applications

- Medical
- LIDAR

Generic Characteristics at $t = 25\text{ }^\circ\text{C}$

	SAT-Series			Units
	Min	Typ	Max	
Wavelength range	700		1100	nm
Peak sensitivity		980		nm

Absolute Maximum Ratings

	SAT800			SAT3000x			Units
	Min	Typ	Max	Min	Typ	Max	
Storage temperature	-55		100	-55		100	°C
Operating temperature	-40		85	-40		85	°C
Reverse current (CW)			200			200	µA
Reverse current (1 sec)			1			1	mA
Forward current (CW)			5			5	mA
Forward current (1 sec)			50			50	mA
Max. power dissipation			60			60	mW
Soldering (15 sec.)			260			260	°C

Electrical Characteristics @ M= 100, 25 °C

	SAT800			SAT3000			Units
	Min	Typ	Max	Min	Typ	Max	
Diameter		800			3000		µm
Breakdown voltage (I _d = 10 µA)		400			400		Volt
Responsivity (M = 100 & λ = 1064 nm)	20	25		30	34		A/W
V _{breakdown} temp coefficient		2.5			2.5		V/°C
Dark current (M = 100)		1	10		5	20	nA
Noise current (M = 100)		0.5	1.5		1	3	pA/ sqrtHz
Capacitance (M = 100)		2			10		pF
Rise time (M = 100)		1			3		nsec

SAT800X:

Fig. 1: Spectral Response

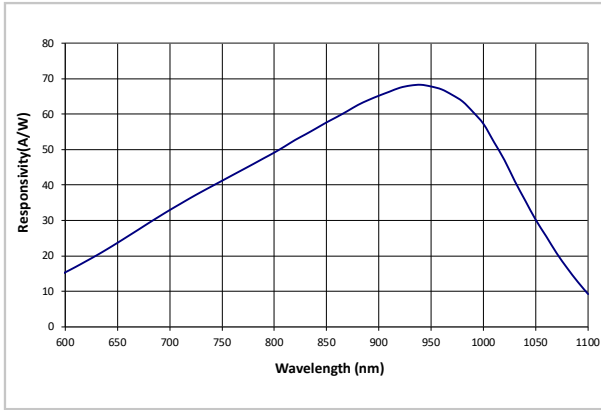


Fig. 2: Quantum Efficiency vs. Wavelength

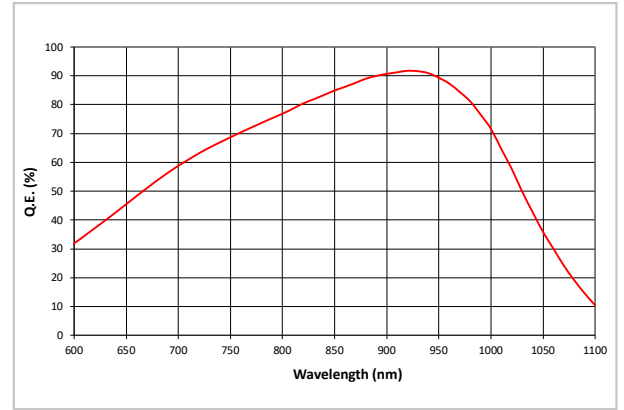


Fig. 3: Typical Dark Current Characteristics

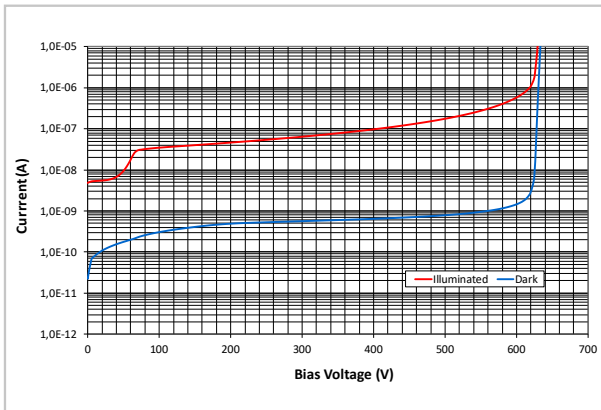


Fig. 4: Gain – Voltage Characteristics

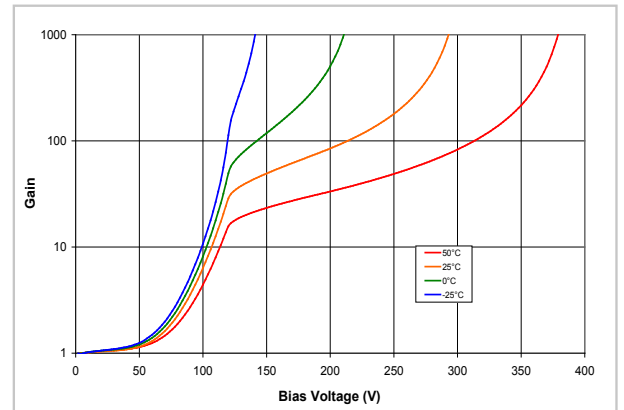


Fig. 5: Capacitance vs. Reverse Voltage

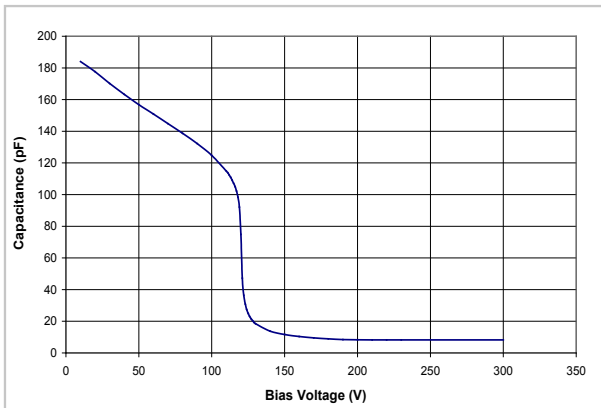
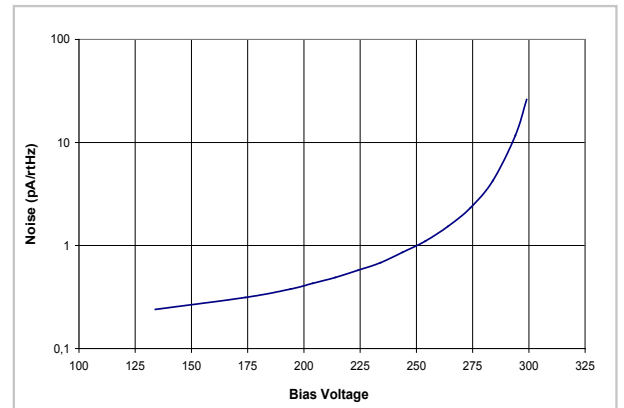


Fig. 6: Typical APD Noise as a Function of Bias Voltage



SAT3000x:

Fig. 7: Spectral Response

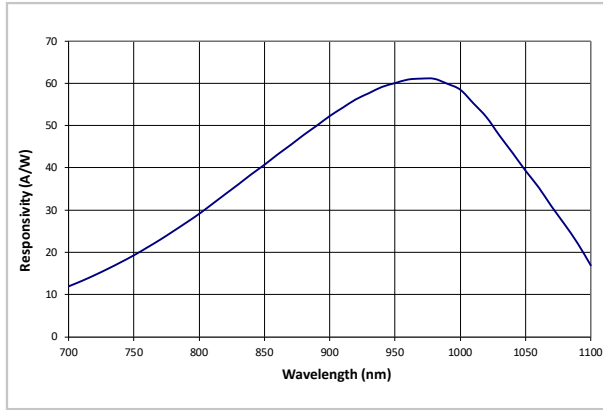


Fig. 8: Quantum Efficiency vs. Wavelength

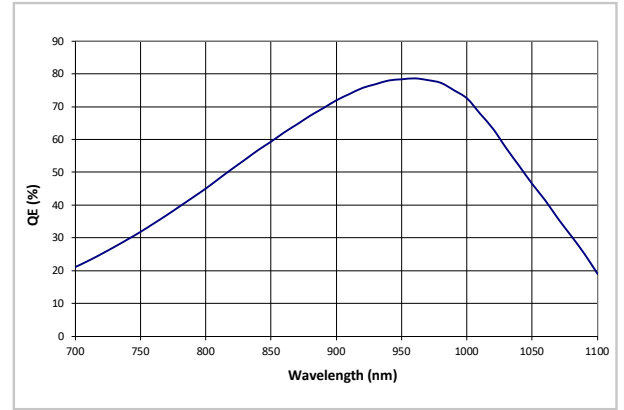


Fig. 9: Typical Dark Current Characteristics

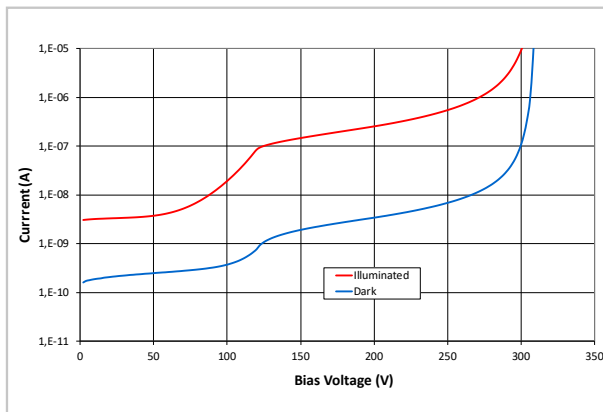


Fig. 10: Gain – Voltage Characteristics

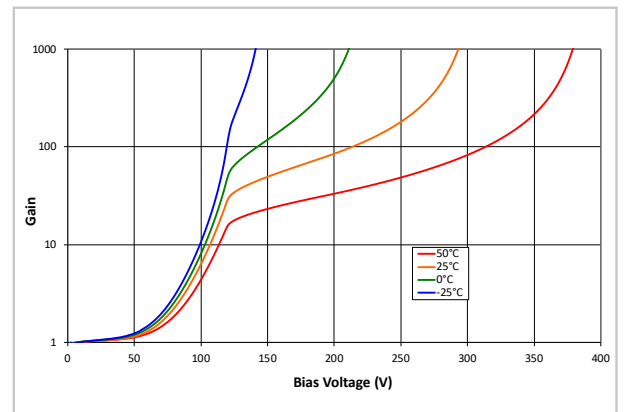


Fig. 11: Capacitance vs. Reverse Voltage

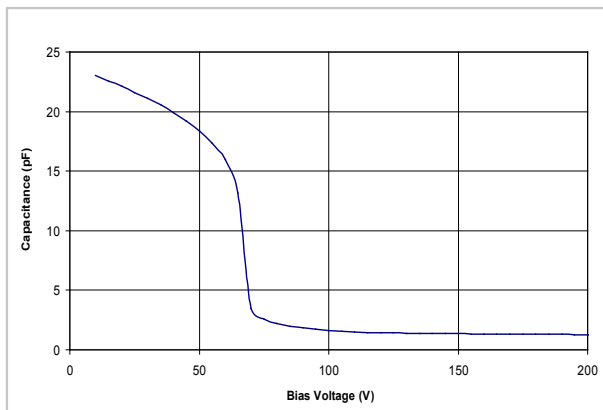
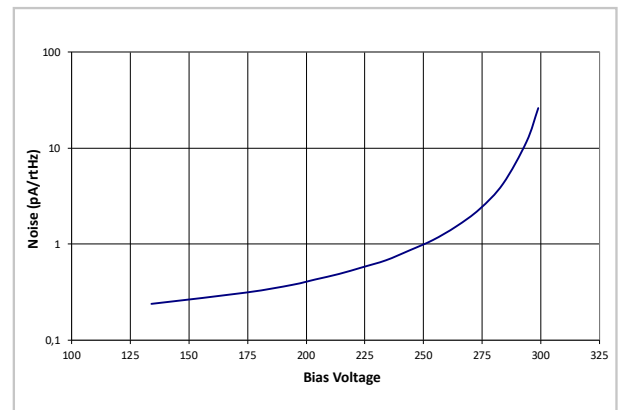
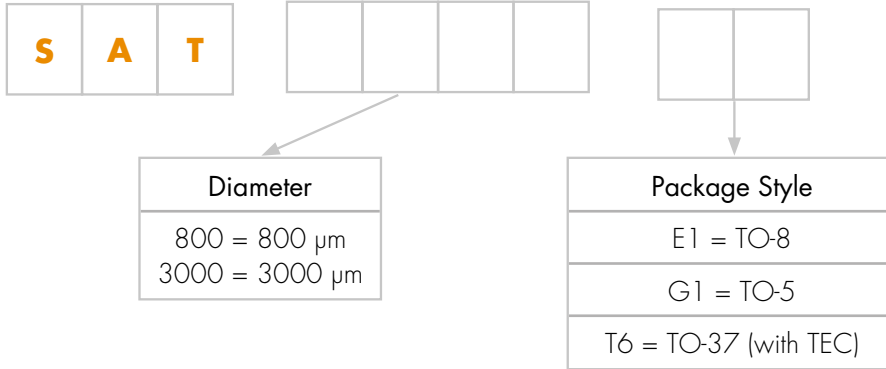


Fig. 12: Typical APD Noise as a Function of Bias Voltage

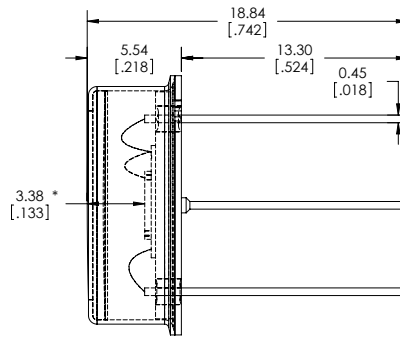
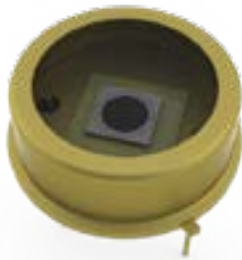


Product Number Designations

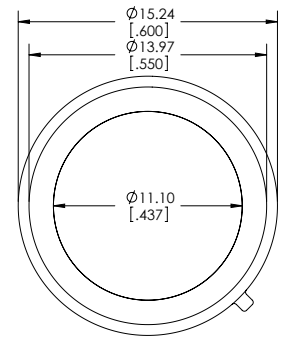


Package Drawings

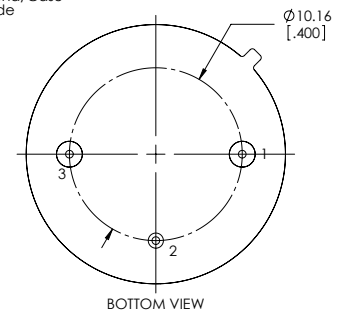
Package E1 TO-8



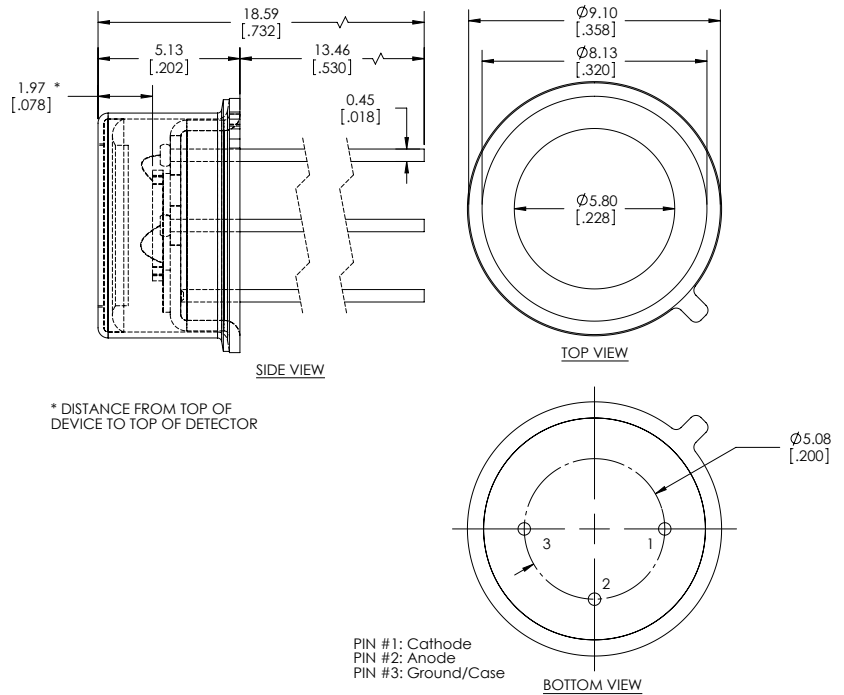
* DISTANCE FROM TOP OF DEVICE TO TOP OF DETECTOR



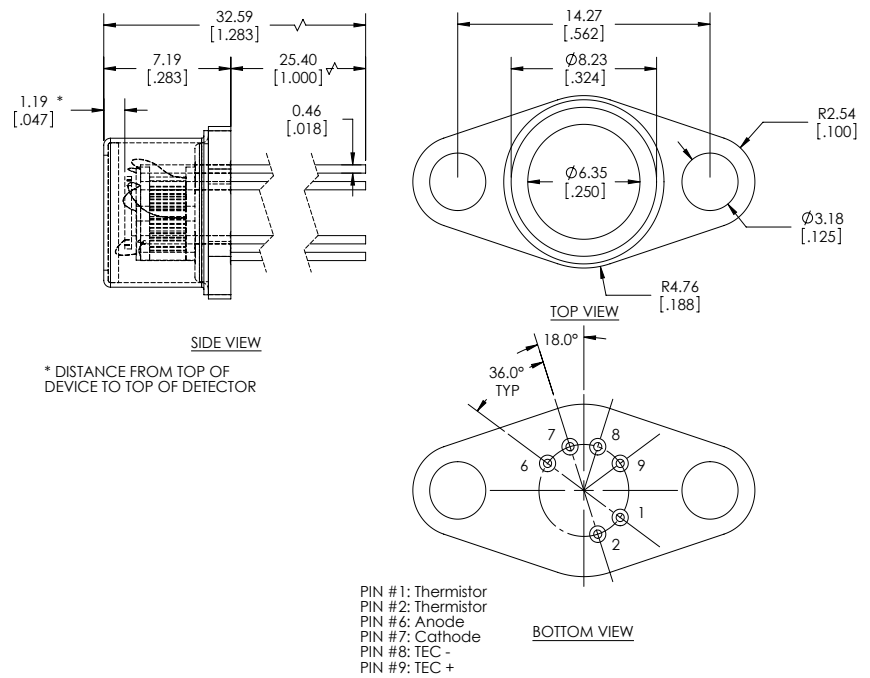
PIN #1: Cathode
 PIN #2: Ground/Case
 PIN #3: Anode



Package G1 TO-5



Package T6 TO-37 (with TEC)



Product Changes

LASER COMPONENTS reserves the right to make changes to the product(s) or information contained herein without notice. No liability is assumed as a result of their use or application.

Ordering Information

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